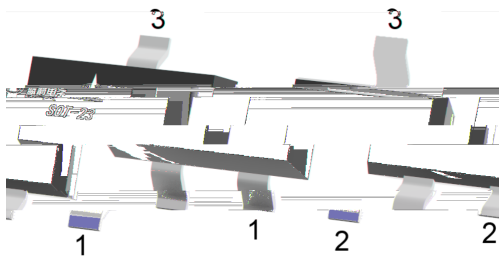
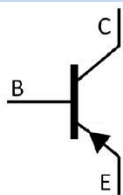


SOT-23 PNP Silicon PNP transistor in a SOT-23 Plastic Package.

P_C , h_{FE} , 9014MG
 Hig P_C and I_C , excellent h_{FE} linearity, complementary pair with 9014MG,HF Product.

low frequency, low noise pre-amplifier.

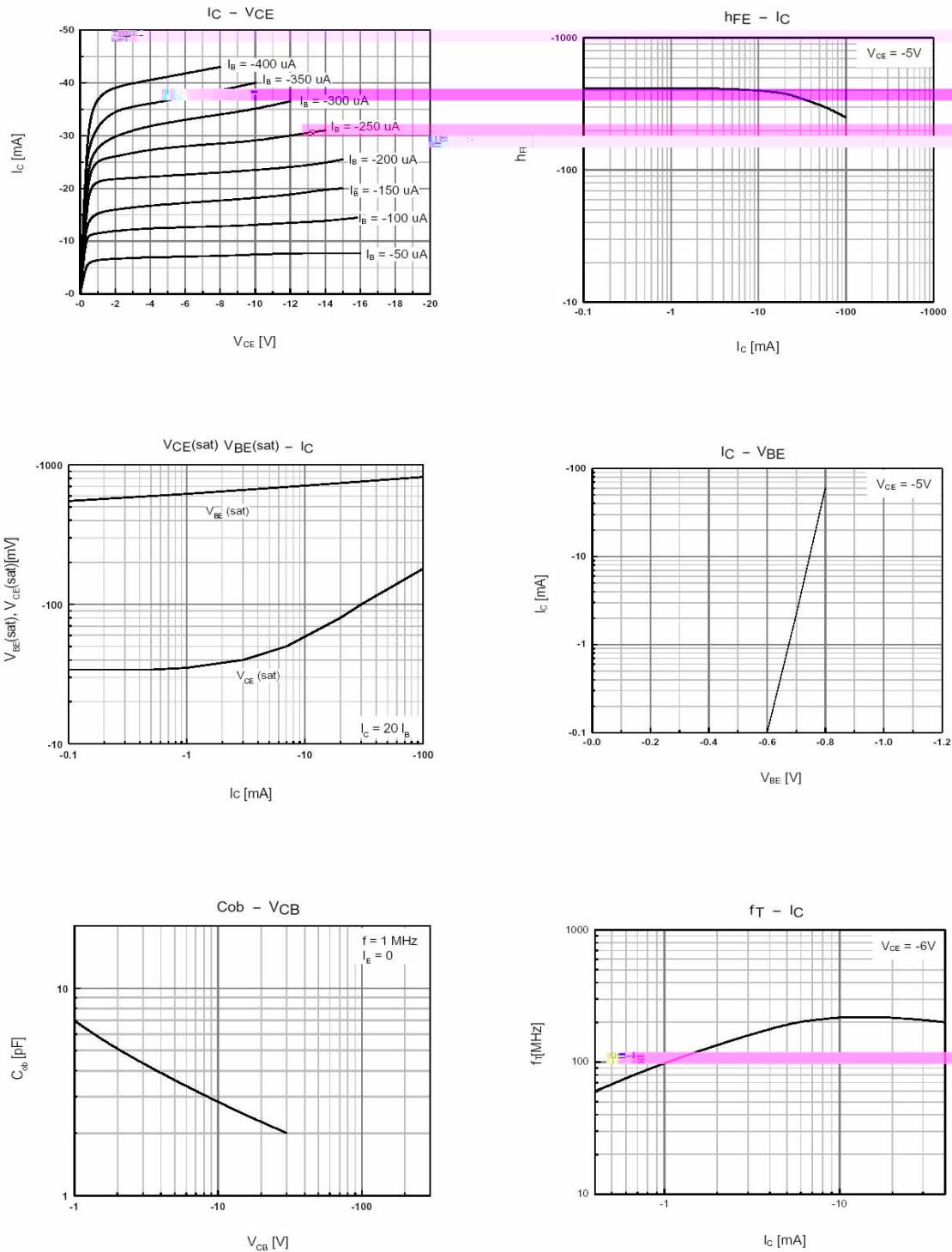


PIN1 Base PIN 2 Emitter PIN 3 Collector

h_{FE} Classifications Symbol	A	B	C	D
h_{FE} Range	60 150	100 300	200 600	400 1000
Marking	GM6A	GM6B	GM6C	GM6D

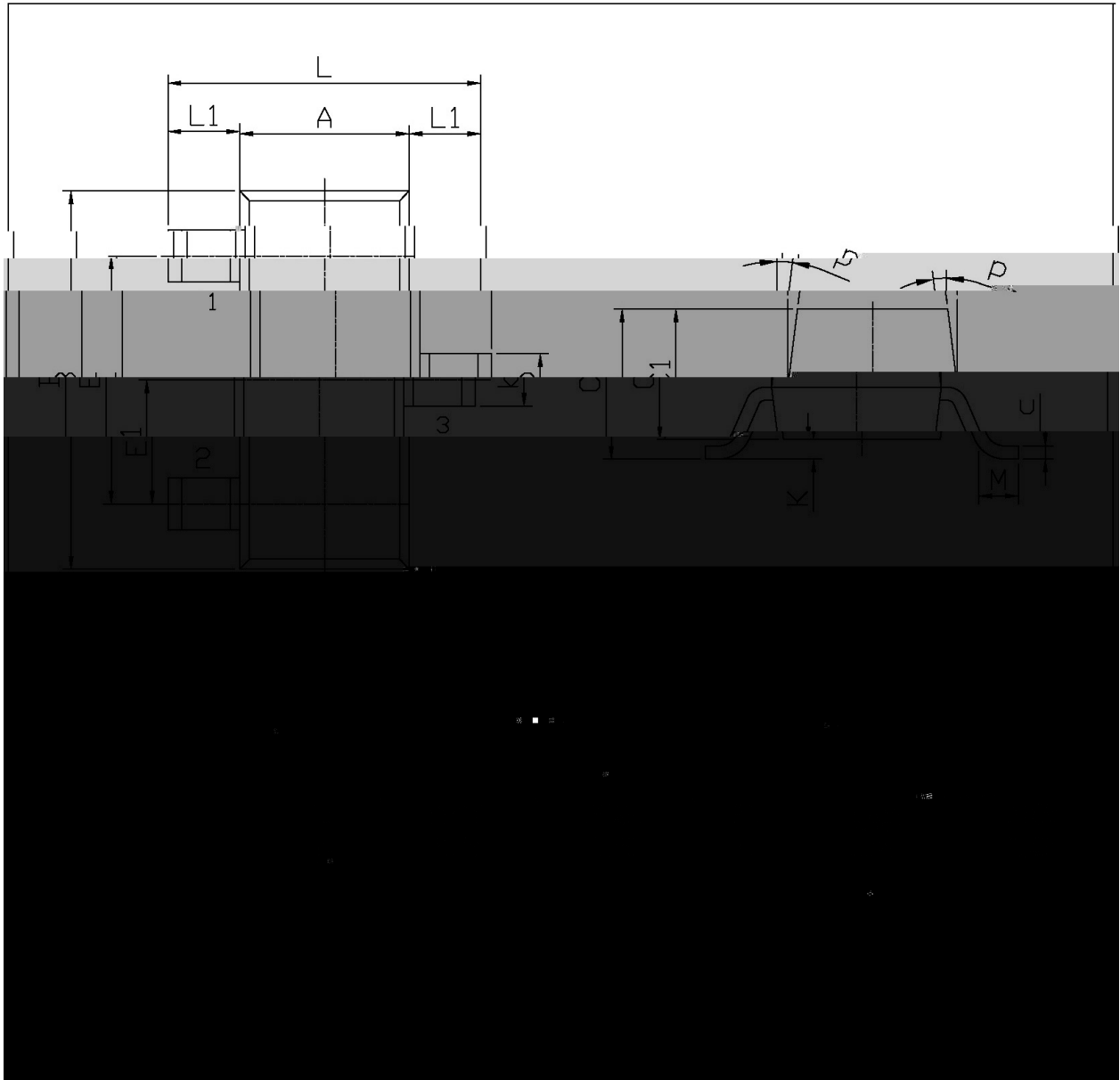
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-50	V
Collector to Emitter Voltage	V_{CEO}	-45	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-100	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

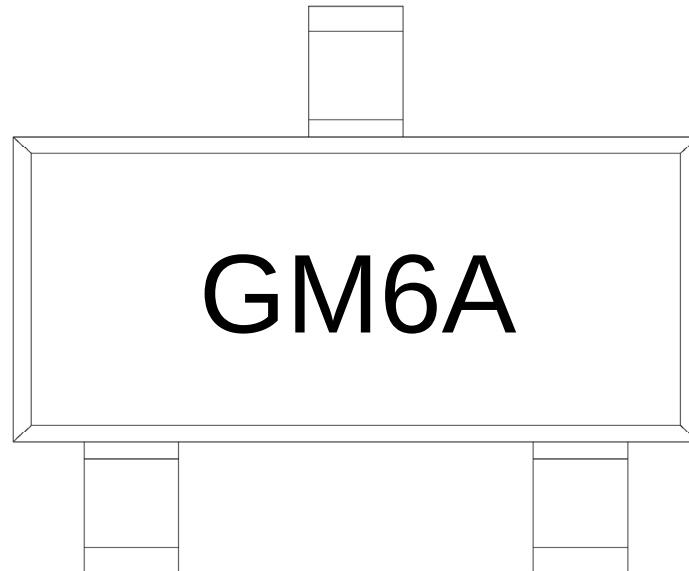
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-0.1mA$ $I_E=0$	-50			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-1.0mA$ $I_B=0$	-45			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-0.1mA$ $I_C=0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-50V$ $I_E=0$			-0.05	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5.0V$ $I_C=0$			-0.05	A
DC Current Gain	h_{FE}	$V_{CE}=-5.0V$ $I_C=-1.0mA$	60		600	
Collector-Emitter Saturation voltage	$V_{CE(sat)}$	$I_C=-100mA$ $I_B=-5.0mA$		-0.2	-0.7	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-100mA$ $I_B=-5.0mA$		-0.82	-1.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=-5.0V$ $I_C=-2.0mA$		-0.65	-0.75	V
Transition Frequency	f_T	$V_{CE}=-5.0V$ $I_C=-10mA$	100	190		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V$ $I_E=0$ $f=1.0MHz$		4.5	7.0	pF
Noise Figure	NF	$V_{CE}=-5.0V$ $I_C=-0.2mA$ $R_g=2.0K$ $f=1.0KHz$ $\Delta f=200Hz$		0.7	10	dB



SOT-23

单位: mm





G

M6

A h_{FE}

Note:

G HF Product Code

M6 Product Type Code

A h_{FE} Classifications Symbol Code

